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L	Hits	Search Text	DB	Time stamp
Number				
1	1561906	low ajd2 temperature and silicon adj3 carbide	USPAT	2003/10/17 10:24
2	6034	low adj2 temperature and silicon adj3	USPAT	2003/10/17
3	1	carbide (low adj2 temperature and silicon adj3	USPAT	10:24 2003/10/17
	_	carbide) and plasma adj2 etch?	**************************************	10:25
4	1767	(low adj2 temperature and silicon adj3 carbide) and plasma	USPAT	2003/10/17 10:25
5	1113	((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen	USPAT	2003/10/17 10:25
6	834	(((low adj2 temperature and silicon adj3	USPAT	2003/10/17 10:25
		carbide) and plasma) and hydrogen) and oxygen		
7	0	((((low adj2 temperature and silicon adj3 carbide) and plasma) and hydrogen) and	USPAT	2003/10/17 10:25
	220	oxygen) and etch? ((((low adj2 temperature and silicon adj3	USPAT	2003/10/17
8	228	carbide) and plasma) and hydrogen) and	USPAI	10:26
9	63	oxygen) and semiconductor adj3 substrate (((((low adj2 temperature and silicon	USPAT	2003/10/17
		adj3 carbide) and plasma) and hydrogen) and oxygen) and semiconductor adj3		10:36
	ľ	substrate) and etchant		
10	0	etch? adj4 silicon adj2 carbide	USPAT	2003/10/17
11	146	etching adj4 silicon adj2 carbide	USPAT	10:36 2003/10/17
				10:36
12	79	(etching adj4 silicon adj2 carbide) and plasma	USPAT	2003/10/17 10:37
13	28	((etching adj4 silicon adj2 carbide) and plasma) and low adj3 temperature	USPAT	2003/10/17 10:44
15	16	((((etching adj4 silicon adj2 carbide)	USPAT	2003/10/17
		and plasma) and low adj3 temperature) and hydrogen) and oxygen		10:44
14	20	(((etching adj4 silicon adj2 carbide) and plasma) and low adj3 temperature) and	USPAT	2003/10/17 10:45
		hydrogen		
-	177	cvd adj3 silicon adj3 carbide	USPAT	2003/10/17 10:23
-	0	(cvd adj3 silicon adj3 carbide) and plasma adj3 etch?	USPAT	2003/05/27 11:28
_	85	(cvd adj3 silicon adj3 carbide) and	USPAT	2003/05/27
_	33	plasma   ((cvd adj3 silicon adj3 carbide) and	USPAT	11:28 2003/05/27
		plasma ) and hydrogen		11:28